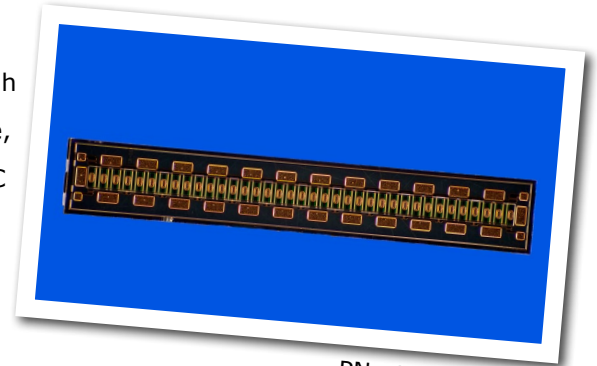


CGHV1J070D

70 W, 18.0 GHz, GaN HEMT Die

Cree's CGHV1J070D is a high voltage gallium nitride (GaN) High Electron Mobility Transistor (HEMT) on a silicon carbide substrate, using a 0.25 μm gate length fabrication process. This GaN-on-SiC product offers superior high frequency, high efficiency features. It is ideal for a variety of applications operating from 10 MHz to 18 GHz at 40 V with a high breakdown voltage.



PN: CGHV1J070D

FEATURES

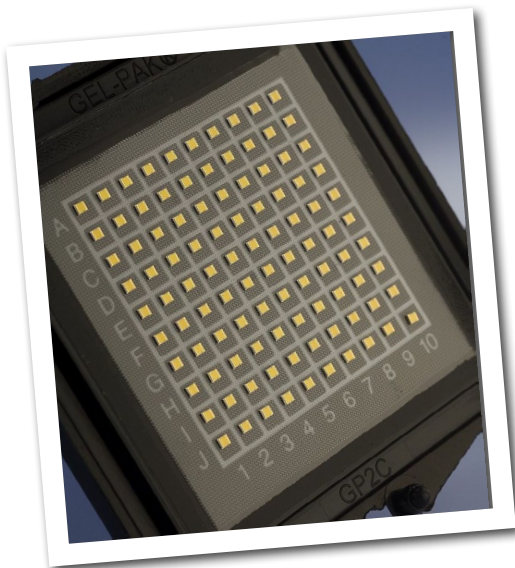
- 17 dB Typ. Small Signal Gain at 10 GHz
- 60% Typ. PAE at 10 GHz
- 70 W Typical Psat
- 40 V Operation
- Up to 18GHz Operation

APPLICATIONS

- Satellite Communications
- PTP Communications Links
- Marine Radar
- Pleasure Craft Radar
- Port Vessel Traffic Services
- Broadband Amplifiers
- High Efficiency Amplifiers

Packaging Information

- Bare die are shipped in Gel-Pak® containers or on tape.
- Non-adhesive tacky membrane immobilizes die during shipment.



Large Signal Models Available for SiC & GaN

Absolute Maximum Ratings (not simultaneous)

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DS}	100	Volts	25°C
Gate-source Voltage	V_{GS}	-10, +2	Volts	25°C
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Forward Gate Current	I_{GMAX}	14.4	mA	25°C
Maximum Drain Current ¹	I_{DMAX}	6.0	A	25°C
Thermal Resistance, Junction to Case (packaged) ²	$R_{\theta JC}$	1.8	°C/W	85°C
Thermal Resistance, Junction to Case (die only) ²	$R_{\theta JC}$	1.1	°C/W	85°C
Mounting Temperature	T_S	320	°C	30 seconds

Note¹ Current limit for long term reliable operation.

Note² Eutectic die attach using 80/20 AuSn mounted to a 60 mil thick CMC carrier.

Electrical Characteristics (Frequency = 10 GHz unless otherwise stated; $T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{(GS)TH}$	-3.8	-3.0	-2.3	V	$V_{DS} = 10\text{ V}, I_D = 14.4\text{ mA}$
Gate Quiescent Voltage	$V_{(GS)Q}$	-	-2.7	-	VDC	$V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA}$
Saturated Drain Current ¹	I_{SAT}	11.5	13.0	-	A	$V_{DS} = 6.0\text{ V}, V_{GS} = 2.0\text{ V}$
Drain-Source Breakdown Voltage	V_{BD}	100	-	-	V	$V_{GS} = -8\text{ V}, I_D = 14.4\text{ mA}$
On Resistance	R_{ON}	-	0.2	-	Ω	$V_{DS} = 0.1\text{ V}, V_{GS} = 0\text{ V}$
Gate Forward Voltage	V_{G-ON}	-	1.85	-	V	$I_{GS} = 14.4\text{ mA}$
RF Characteristics						
Small Signal Gain	G_{SS}	-	17	-	dB	$V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA}$
Saturated Power Output ¹	P_{SAT}	-	70	-	W	$V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA}$
Drain Efficiency ²	η	-	60	-	%	$V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA}$
Intermodulation Distortion	IM3	-	-30	-	dBc	$V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA}, P_{OUT} = 70\text{ W PEP}$
Output Mismatch Stress	VSWR	-	-	10 : 1	Ψ	No damage at all phase angles, $V_{DD} = 40\text{ V}, I_{DQ} = 720\text{ mA},$ $P_{OUT} = 70\text{ W CW}$
Dynamic Characteristics						
Input Capacitance	C_{GS}	-	24.0	-	pF	$V_{DS} = 40\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$
Output Capacitance	C_{DS}	-	4.2	-	pF	$V_{DS} = 40\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$
Feedback Capacitance	C_{GD}	-	0.6	-	pF	$V_{DS} = 40\text{ V}, V_{GS} = -8\text{ V}, f = 1\text{ MHz}$

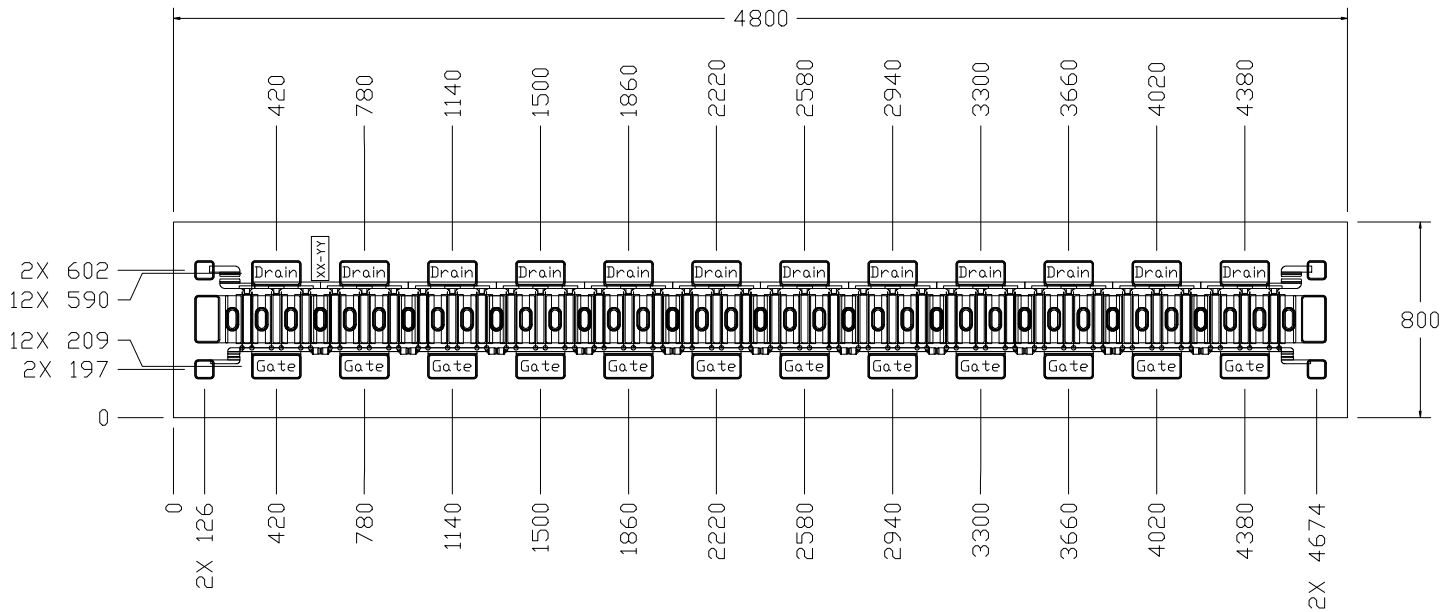
Notes:

¹ Scaled from PCM unit cell.

¹ P_{SAT} is defined as $I_G = 1.44\text{ mA}$.

² Drain Efficiency = P_{OUT} / P_{DC}

Die Dimensions (units in microns)



Overall die size 800 x 4800 (+0/-50) microns, die thickness 100 (+/-10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Pad	Size (microns)
Drain	200 x 100
Gate	200 x 100
Interconnect	80 x 80

Assembly Notes:

- Recommended solder is AuSn (80/20) solder. Refer to Cree's website for the Eutectic Die Bond Procedure application note at http://www.cree.com/products/wireless_documents.asp
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.
- Use the die label (XX-YY) for correct orientation.

Gmax and K Factor

Figure 1. CGHV1J070D - Stability with Gmax and K Factor
 $V_{DD} = 40\text{ V}, I_{DS} = 360\text{ mA}$

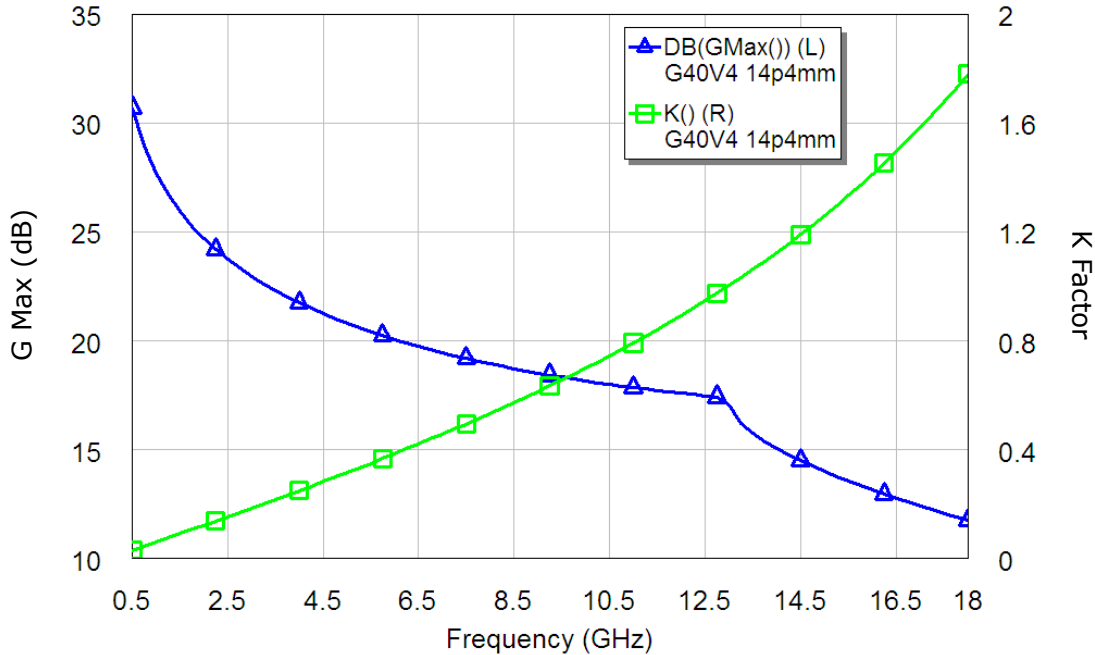
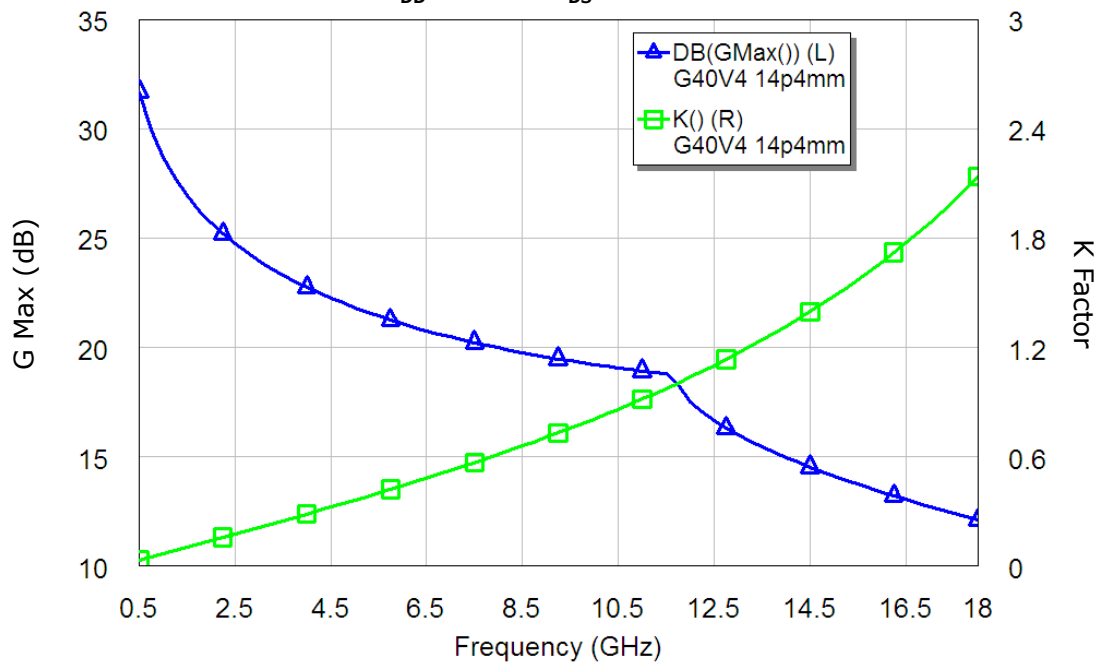


Figure 2. CGHV1J070D - Stability with Gmax and K Factor
 $V_{DD} = 40\text{ V}, I_{DS} = 720\text{ mA}$



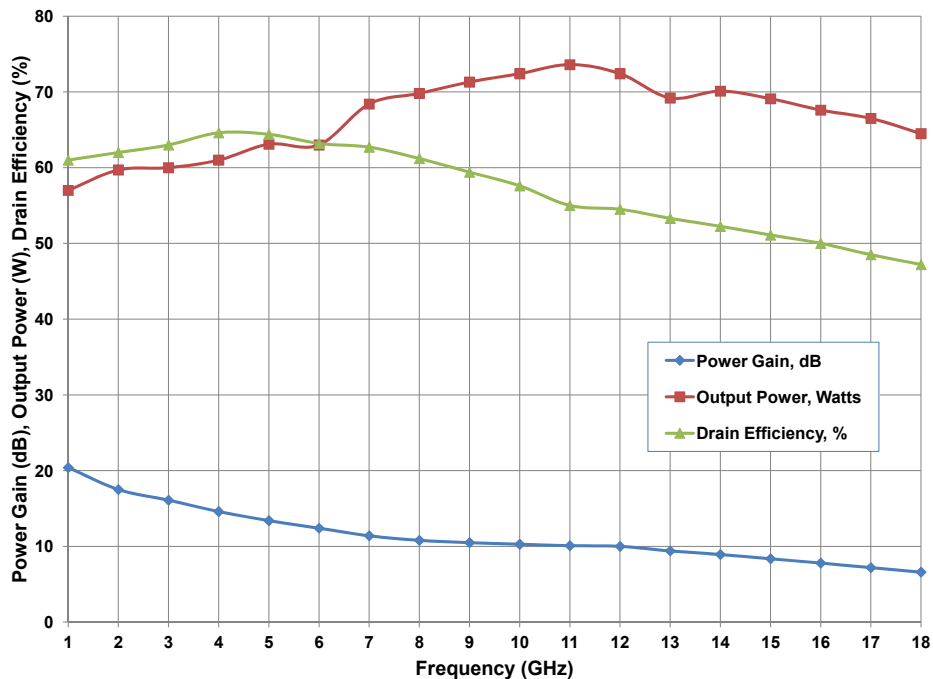
Source and Load Impedances

Frequency (GHz)	Source Impedance (ohms)	Load Impedance (ohms)	Series Gate Stability Resistor (ohms)
1.0	2.77 + j3.567	11 + j8.57	2.40
2.0	1.33 + j1.78	5.83 + j8.15	1.15
3.0	0.76 + j1.11	3.06 + j6.97	0.65
4.0	0.627 + j0.778	2.06 + j5.82	0.45
5.0	0.55 + j0.57	1.48 + j4.88	0.325
6.0	0.458 + j0.41	1.07 + j4.16	0.250
7.0	0.465 + j0.296	0.896 + j3.5	0.180
8.0	0.453 + j0.19	0.785 + j3.2	0.125
9.0	0.399 + j0.096	0.71 + j2.86	0.090
10.0	0.328 + j0.01	0.643 + j2.56	0.060
11.0	0.245 - j0.018	0.61 + j2.32	0.035
12.0	0.173 - j0.03	0.52 + j2.06	0.013
13.0	0.247 - j0.085	0.474 + j1.917	0
14.0	0.149 - j0.19	0.417 + j1.73	0
15.0	0.143 - j0.268	0.377 + j1.57	0
16.0	0.144 - j0.34	0.34 + j1.43	0
17.0	0.142 - j0.41	0.31 + j1.29	0
18.0	0.158 - j0.478	0.279 + j1.18	0

Table 1.

Note: $V_{DD} = 40\text{ V}$, $I_{DQ} = 535\text{ mA}$.

Figure 3. CGHV1J070D - Power Gain, Output Power and Drain Efficiency using Source and Load Pull Impedances (Series gate stability resistor values chosen to make $K > 1$)





Typical S-Parameters for CGHV1J070D
 (Small Signal, $V_{DS} = 40\text{ V}$, $I_{DQ} = 360\text{ mA}$, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.944	-165.60	12.49	87.69	0.011	-1.78	0.603	-167.23
1.00 GHz	0.947	-172.19	6.08	75.58	0.010	-13.31	0.637	-166.40
1.50 GHz	0.952	-174.26	3.86	66.38	0.010	-21.95	0.680	-164.85
2.00 GHz	0.957	-175.28	2.72	58.56	0.009	-29.21	0.725	-164.11
2.50 GHz	0.962	-175.92	2.03	51.82	0.009	-35.39	0.766	-164.10
3.00 GHz	0.967	-176.39	1.57	45.99	0.008	-40.66	0.802	-164.56
3.50 GHz	0.971	-176.78	1.25	40.95	0.007	-45.14	0.832	-165.26
4.00 GHz	0.974	-177.11	1.02	36.56	0.007	-48.97	0.857	-166.06
4.50 GHz	0.977	-177.40	0.84	32.73	0.006	-52.24	0.877	-166.88
5.00 GHz	0.980	-177.67	0.70	29.35	0.006	-55.05	0.894	-167.69
5.50 GHz	0.982	-177.91	0.60	26.36	0.005	-57.47	0.908	-168.45
6.00 GHz	0.983	-178.12	0.52	23.69	0.005	-59.58	0.919	-169.16
6.50 GHz	0.985	-178.32	0.45	21.29	0.005	-61.41	0.928	-169.82
7.00 GHz	0.986	-178.51	0.39	19.11	0.004	-63.02	0.936	-170.42
7.50 GHz	0.987	-178.68	0.35	17.12	0.004	-64.43	0.943	-170.98
8.00 GHz	0.988	-178.84	0.31	15.29	0.004	-65.68	0.949	-171.49
8.50 GHz	0.989	-178.99	0.28	13.61	0.004	-66.79	0.953	-171.96
9.00 GHz	0.989	-179.13	0.25	12.04	0.003	-67.77	0.958	-172.40
9.50 GHz	0.990	-179.27	0.22	10.58	0.003	-68.65	0.961	-172.80
10.00 GHz	0.990	-179.40	0.20	9.21	0.003	-69.42	0.964	-173.18
10.50 GHz	0.991	-179.52	0.19	7.92	0.003	-70.12	0.967	-173.52
11.00 GHz	0.991	-179.63	0.17	6.70	0.003	-70.74	0.970	-173.85
11.50 GHz	0.991	-179.75	0.16	5.55	0.003	-71.29	0.972	-174.15
12.00 GHz	0.992	-179.85	0.15	4.45	0.003	-71.77	0.974	-174.43
12.50 GHz	0.992	-179.96	0.14	3.40	0.002	-72.20	0.975	-174.70
13.00 GHz	0.992	179.94	0.13	2.39	0.002	-72.58	0.977	-174.95
13.50 GHz	0.992	179.84	0.12	1.43	0.002	-72.91	0.978	-175.19
14.00 GHz	0.992	179.75	0.11	0.50	0.002	-73.20	0.979	-175.41
14.50 GHz	0.993	179.65	0.10	-0.39	0.002	-73.43	0.980	-175.62
15.00 GHz	0.993	179.56	0.10	-1.26	0.002	-73.63	0.981	-175.82
15.25 GHz	0.993	179.52	0.09	-1.68	0.002	-73.71	0.982	-175.92
15.50 GHz	0.993	179.47	0.09	-2.09	0.002	-73.79	0.982	-176.01
15.75 GHz	0.993	179.43	0.09	-2.50	0.002	-73.85	0.983	-176.11
16.00 GHz	0.993	179.39	0.09	-2.90	0.002	-73.90	0.983	-176.20
16.25 GHz	0.993	179.34	0.08	-3.30	0.002	-73.95	0.983	-176.28
16.50 GHz	0.993	179.30	0.08	-3.69	0.002	-73.98	0.984	-176.37
16.75 GHz	0.993	179.26	0.08	-4.07	0.002	-74.00	0.984	-176.45
17.00 GHz	0.993	179.21	0.08	-4.45	0.002	-74.02	0.985	-176.54
17.25 GHz	0.993	179.17	0.07	-4.82	0.002	-74.02	0.985	-176.62
17.50 GHz	0.993	179.13	0.07	-5.19	0.001	-74.01	0.985	-176.70
17.75 GHz	0.993	179.09	0.07	-5.56	0.001	-73.99	0.985	-176.77
18.00 GHz	0.993	179.05	0.07	-5.92	0.001	-73.97	0.986	-176.85

To download the s-parameters in s2p format, go to the [CGHV1J070D Product Page](#) and click on the documentation tab.



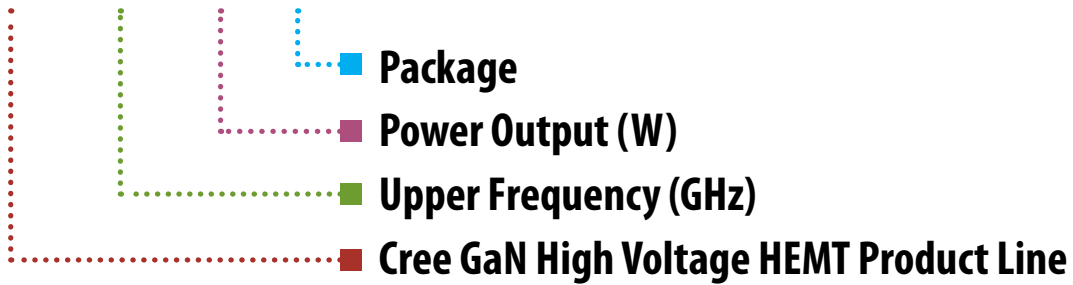
Typical S-Parameters for CGHV1J070D
 (Small Signal, $V_{DS} = 40\text{ V}$, $I_{DQ} = 720\text{ mA}$, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.956	-167.23	12.34	87.98	0.008	-1.48	0.639	-170.66
1.00 GHz	0.958	-173.22	6.04	77.07	0.008	-11.78	0.664	-169.66
1.50 GHz	0.961	-175.13	3.87	68.67	0.008	-19.59	0.696	-168.00
2.00 GHz	0.964	-176.05	2.76	61.38	0.007	-26.29	0.731	-166.94
2.50 GHz	0.968	-176.62	2.08	54.97	0.007	-32.11	0.766	-166.50
3.00 GHz	0.971	-177.03	1.63	49.32	0.007	-37.17	0.797	-166.52
3.50 GHz	0.974	-177.36	1.31	44.34	0.006	-41.56	0.825	-166.85
4.00 GHz	0.977	-177.64	1.07	39.94	0.006	-45.36	0.848	-167.34
4.50 GHz	0.979	-177.89	0.89	36.05	0.005	-48.66	0.868	-167.91
5.00 GHz	0.981	-178.11	0.75	32.60	0.005	-51.52	0.885	-168.52
5.50 GHz	0.983	-178.31	0.64	29.50	0.005	-54.01	0.899	-169.13
6.00 GHz	0.984	-178.50	0.55	26.72	0.004	-56.19	0.910	-169.72
6.50 GHz	0.986	-178.67	0.48	24.21	0.004	-58.10	0.920	-170.28
7.00 GHz	0.987	-178.83	0.42	21.92	0.004	-59.77	0.929	-170.81
7.50 GHz	0.987	-178.98	0.38	19.83	0.004	-61.25	0.936	-171.30
8.00 GHz	0.988	-179.12	0.34	17.91	0.003	-62.56	0.942	-171.76
8.50 GHz	0.989	-179.26	0.30	16.13	0.003	-63.71	0.948	-172.19
9.00 GHz	0.990	-179.38	0.27	14.48	0.003	-64.74	0.952	-172.60
9.50 GHz	0.990	-179.51	0.25	12.93	0.003	-65.64	0.956	-172.97
10.00 GHz	0.990	-179.62	0.22	11.49	0.003	-66.45	0.960	-173.32
10.50 GHz	0.991	-179.73	0.20	10.13	0.003	-67.16	0.963	-173.65
11.00 GHz	0.991	-179.84	0.19	8.84	0.002	-67.79	0.965	-173.96
11.50 GHz	0.991	-179.94	0.17	7.62	0.002	-68.34	0.968	-174.25
12.00 GHz	0.992	179.96	0.16	6.46	0.002	-68.82	0.970	-174.52
12.50 GHz	0.992	179.86	0.15	5.36	0.002	-69.23	0.972	-174.77
13.00 GHz	0.992	179.77	0.14	4.30	0.002	-69.58	0.974	-175.02
13.50 GHz	0.992	179.67	0.13	3.29	0.002	-69.88	0.975	-175.25
14.00 GHz	0.993	179.58	0.12	2.32	0.002	-70.12	0.976	-175.46
14.50 GHz	0.993	179.50	0.11	1.38	0.002	-70.30	0.978	-175.67
15.00 GHz	0.993	179.41	0.11	0.48	0.002	-70.44	0.979	-175.86
15.25 GHz	0.993	179.37	0.10	0.03	0.002	-70.48	0.979	-175.96
15.50 GHz	0.993	179.32	0.10	-0.40	0.002	-70.52	0.980	-176.05
15.75 GHz	0.993	179.28	0.10	-0.82	0.001	-70.54	0.980	-176.14
16.00 GHz	0.993	179.24	0.09	-1.24	0.001	-70.54	0.981	-176.23
16.25 GHz	0.993	179.20	0.09	-1.66	0.001	-70.53	0.981	-176.32
16.50 GHz	0.993	179.16	0.09	-2.06	0.001	-70.51	0.982	-176.40
16.75 GHz	0.993	179.12	0.09	-2.46	0.001	-70.48	0.982	-176.48
17.00 GHz	0.993	179.08	0.08	-2.86	0.001	-70.43	0.983	-176.56
17.25 GHz	0.993	179.04	0.08	-3.25	0.001	-70.37	0.983	-176.64
17.50 GHz	0.993	179.00	0.08	-3.63	0.001	-70.29	0.983	-176.72
17.75 GHz	0.993	178.96	0.08	-4.01	0.001	-70.20	0.984	-176.80
18.00 GHz	0.993	178.92	0.08	-4.39	0.001	-70.09	0.984	-176.87

To download the s-parameters in s2p format, go to the [CGHV1J070D Product Page](#) and click on the documentation tab.

Part Number System

CGHV1J070D



Parameter	Value	Units
Lower Frequency	DC	GHz
Upper Frequency ¹	18.0	GHz
Power Output	70	W
Package	Bare Die	-

Table 1.

Note¹: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Table 2.

Disclaimer

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For more information, please contact:

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
www.cree.com/wireless

Sarah Miller
Marketing
Cree, RF Components
1.919.407.5302

Ryan Baker
Cree, Marketing, RF Components
1.919.407.7816

Tom Dekker
Cree, Sales Director, RF Components
1.919.313.5639

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)
Email: org@lifeelectronics.ru